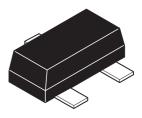


# ZXTP19020CFF 20V, SOT23F, PNP medium power transistor

### Summary:

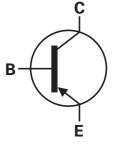
BV<sub>CEO</sub> > -20V BV<sub>ECO</sub> > -5V I<sub>C(cont)</sub> = -5A V<sub>CE(sat)</sub> < 40mV @ 100mA R<sub>CE(sat)</sub> = 21mΩ P<sub>D</sub> = 1.5W



Complementary part number ZXTN19020CFF

## Description

Advanced process capability has been used to maximize the performance of this transistor. The SOT23F package is compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.



Pinout - top view

C

E

В

### Features

- High gain
- Low saturation voltage
- Low profile high dissipation package

## Applications

- Battery charging
- Load switch
- DC-DC converters

## **Ordering information**

Device	Reel size	Tape width	Quantity
	(inches)	(mm)	per reel
ZXTP19020CFFTA	7	8	3000

## **Device marking**

1D7



## Absolute maximum ratings

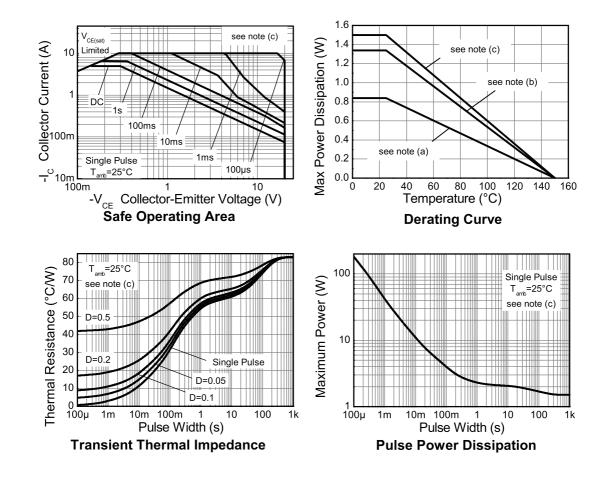
Parameter	Symbol	Limit	Unit	
Collector-base voltage	V <sub>CBO</sub>	-25	V	
Collector-emitter voltage	V <sub>CEO</sub>	-20	V	
Emitter-collector voltage (reverse blocking)	V <sub>ECO</sub>	-5	V	
Emitter-base voltage	V <sub>EBO</sub>	-7	V	
Continuous collector current <sup>(c)</sup>	۱ <sub>C</sub>	-5	А	
Peak pulse current	I <sub>СМ</sub>	-10	А	
Base current	I <sub>B</sub>	-1	А	
Power dissipation at T <sub>amb</sub> =25°C <sup>(a)</sup>	PD	0.84	W	
Linear derating factor		6.72	mW/°C	
Power dissipation at T <sub>amb</sub> =25°C <sup>(b)</sup>	PD	1.34	W	
Linear derating factor		10.72	mW/°C	
Power dissipation at $T_{amb} = 25^{\circ}C^{(c)}$	PD	1.5	W	
Linear derating factor		12.0	mW/°C	
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$	PD	2.0	W	
Linear derating factor		16.0	mW/°C	
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C	
Thermal resistance				
Parameter	Symbol	Value	Unit	
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	149.3	°C/W	
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	93.4	°C/W	
Junction to ambient <sup>(c)</sup>	$R_{\Theta JA}$	83.3	°C/W	
Junction to ambient <sup>(d)</sup>	$R_{\Theta JA}$	60	°C/W	

#### NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (d) As (c) above measured at t<5secs.

## Characteristics



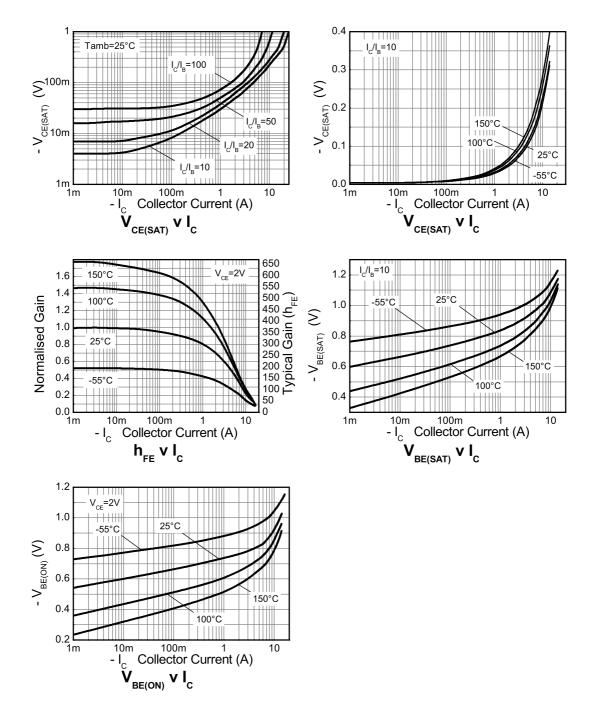
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	-25	-45		V	I <sub>C</sub> = -100μA
Collector-emitter breakdown voltage (base open)	BV <sub>CEO</sub>	-20	-30		V	I <sub>C</sub> = -10mA <sup>(*)</sup>
Emitter-base breakdown voltage	$BV_{EBO}$	-7	-8.3		V	I <sub>E</sub> = -100μA
Emitter-collector breakdown voltage (reverse blocking)	BV <sub>ECX</sub>	-6	-8.3		V	$\begin{array}{l} I_{E} = -100 \mu A,  R_{BC} \leq 1 \mathrm{k} \Omega   \text{or} \\ 0.25 V < V_{BC}  < -0.25 V \end{array}$
Emitter-collector breakdown voltage (base open)	BV <sub>ECO</sub>	-5	-8.5		V	I <sub>E</sub> = -100μA,
Collector-base cut-off current	I <sub>CBO</sub>		<-1	-50	nA	V <sub>CB</sub> = -20V
				-20	μA	$V_{CB} = -20V, T_{amb} = 100^{\circ}C$
Emitter-base cut-off current	I <sub>EBO</sub>		<-1	-50	nA	V <sub>EB</sub> = -5.6V
Collector-emitter saturation	V <sub>CE(sat)</sub>		-30	-40	mV	$I_{C} = -1A, I_{B} = -100 \text{mA}^{(*)}$
voltage			-50	-70	mV	I <sub>C</sub> = -1A, I <sub>B</sub> = -20mA <sup>(*)</sup>
			-75	-120	mV	$I_{C} = -2A, I_{B} = -40mA^{(*)}$
			-105	-135	mV	I <sub>C</sub> = -5A, I <sub>B</sub> = -500mA <sup>(*)</sup>
Base-emitter saturation voltage	$V_{BE(sat)}$		-925	-1050	mV	$I_{C} = -5A, I_{B} = -500 \text{mA}^{(*)}$
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		-815	-950	mV	$I_{C} = -5A, V_{CE} = -2V^{(*)}$
Static forward current transfer	h <sub>FE</sub>	200	350	500		$I_{C} = -100 \text{mA}, V_{CE} = -2V^{(*)}$
ratio		170	300			$I_{C} = -1A, V_{CE} = -2V^{(*)}$
		110	180			$I_{C} = -5A, V_{CE} = -2V^{(*)}$
Transition frequency	f <sub>T</sub>		200		MHz	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -10V f = 100MHz
Output capacitance	C <sub>obo</sub>		52	70	pF	V <sub>CB</sub> = -10V, f = 1MHz <sup>(*)</sup>
Delay time	t <sub>d</sub>		66.8		ns	V <sub>CC</sub> = -15V.
Rise time	t <sub>r</sub>		74.9		ns	$I_{\rm C} = -750 {\rm mA},$
Storage time	t <sub>s</sub>		226		ns	I <sub>B1</sub> = 15mA, I <sub>B2</sub> = -15mA.
Fall time	t <sub>f</sub>		85.5		ns	

## Electrical characteristics (at $T_{amb}$ = 25°C unless otherwise stated)

### NOTES:

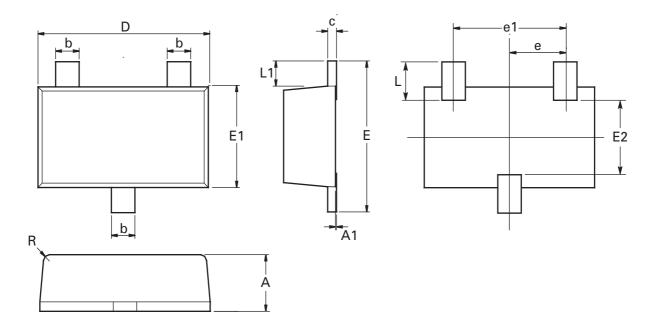
(\*) Measured under pulsed conditions. Pulse width  ${\leq}300\mu s;$  duty cycle  ${\leq}2\%.$ 

## **Typical characteristics**



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## Package outline - SOT23F



Dim.	Millim	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	0.80	1.00	0.0315	0.0394	E	2.30	2.50	0.0906	0.0984
A1	0.00	0.10	0.00	0.0043	E1	1.50	1.70	0.0590	0.0669
b	0.35	0.45	0.0153	0.0161	E2	1.10	1.26	0.0433	0.0496
С	0.10	0.20	0.0043	0.0079	L	0.48	0.68	0.0189	0.0268
D	2.80	3.00	0.1102	0.1181	L1	0.30	0.50	0.0153	0.0161
е	0.95	ref	0.037	74 ref	R	0.05	0.15	0.0019	0.0059
e1	1.80	2.00	0.0709	0.0787	0	0°	12°	0°	12°

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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